



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of)

Group Art Unit: 2822

Yashuhiko TAKEMURA et al.)

Examiner: Yung A. Lin

Serial No.: 09/321,715)

Filed: May 28, 1999)

For: SEMICONDUCTOR DEVICE)
AND PROCESS FOR FABRICATING)
THE SAME)

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents and Trademarks, Washington, D.C. 20231, on

4-4-00.

Deborah J. Zonne

AMENDMENT

Assistant Commissioner for Patents
Washington, D. C. 20231

Sir:

In response to the Office Action mailed January 4, 2000, please amend the above-identified application as follows.

IN THE CLAIMS:

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APR 13 2000

TECHNOLOGY CENTER 2800

Kindly amend claims 1, 5, 9, 13, 17, 21, 25, 27, 29, 33, 37, 35, 41, 43, 45, 49, 50, 52, 56, 57, 59, 63, 64, 66, 67, 70-72, 74, 78-80, 82, 86-88, and 90 as follows:

1. (Amended) A method of manufacturing a semiconductor device having a plurality of thin film transistors, comprising the steps of:
forming a semiconductor film comprising silicon over a glass substrate;
crystallizing said semiconductor film; and

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216.00 OP

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Andt
J. McInnis
4/14/00

Sup B